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Freescale Semiconductor - MPC8547EVTAQGD Datasheet

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8547evtaqgd

Email: info@E-XFL.COM
Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^{2}C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^{2}C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^{2}C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^{2}C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)

  - Single inbound doorbell message structure
  - Facility to accept port-write messages
- PCI Express interface
  - PCI Express 1.0a compatible
  - Supports x8,x4,x2, and x1 link widths
  - Auto-detection of number of connected lanes
  - Selectable operation as root complex or endpoint
  - Both 32- and 64-bit addressing
  - 256-byte maximum payload size
  - Virtual channel 0 only
  - Traffic class 0 only
  - Full 64-bit decode with 32-bit wide windows
- Pin multiplexing for the high-speed I/O interfaces supports one of the following configurations:
  - 8 PCI Express
  - 4 PCI Express and 4 serial RapidIO
- Power management
  - Supports power saving modes: doze, nap, and sleep
  - Employs dynamic power management, which automatically minimizes power consumption of blocks when they are idle
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the eight counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- JTAG boundary scan, designed to comply with IEEE Std. 1149.1™

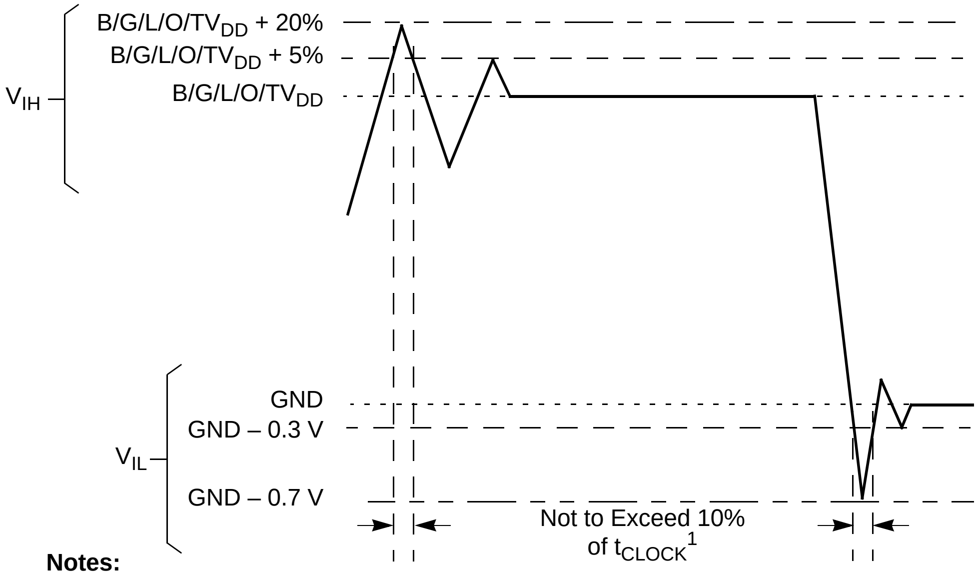
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	Tj	0 to 105	°C	—

Notes:

1. This voltage is the input to the filter discussed in Section 22.2, “PLL Power Supply Filtering,” and not necessarily the voltage at the AV_{DD} pin, which may be reduced from V_{DD} by the filter.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** L/TV_{IN} must not exceed L/TV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

The following figure shows the undershoot and overshoot voltages at the interfaces of this device.



Notes:

1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I^2C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For LBIU, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI*n*_CLK or SYSCLK.
   For SerDes, t_{CLOCK} references SD_REF_CLK.
2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}/BV_{DD}/TV_{DD}$

The core voltage must always be provided at nominal 1.1 V. Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR SDRAM interface uses a single-ended differential receiver referenced the externally supplied MV_{REF} signal (nominally set to $GV_{DD}/2$) as is appropriate for the SSTL2 electrical signaling standard.

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

4.5 Platform to FIFO Restrictions

Note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency ≤ platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency ≤ platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 167 MHz.

4.6 Platform Frequency Requirements for PCI-Express and Serial RapidIO

The CCB clock frequency must be considered for proper operation of the high-speed PCI-Express and Serial RapidIO interfaces as described below.

For proper PCI Express operation, the CCB clock frequency must be greater than:

$$\frac{527\text{ MHz} \times (\text{PCI-Express link width})}{8}$$

See *MPC8548ERM, Rev. 2, PowerQUICC III Integrated Processor Family Reference Manual,* Section 18.1.3.2, “Link Width,” for PCI Express interface width details.

For proper serial RapidIO operation, the CCB clock frequency must be greater than:

$$\frac{2 \times (0.80) \times (\text{Serial RapidIO interface frequency}) \times (\text{Serial RapidIO link width})}{64}$$

See *MPC8548ERM, Rev. 2, PowerQUICC III Integrated Processor Family Reference Manual,* Section 17.4, “1x/4x LP-Serial Signal Descriptions,” for serial RapidIO interface width and frequency details.

4.7 Other Input Clocks

For information on the input clocks of other functional blocks of the platform see the specific section of this document.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \le V_{OUT} \le GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

Figure 8 shows the GMII transmit AC timing diagram.

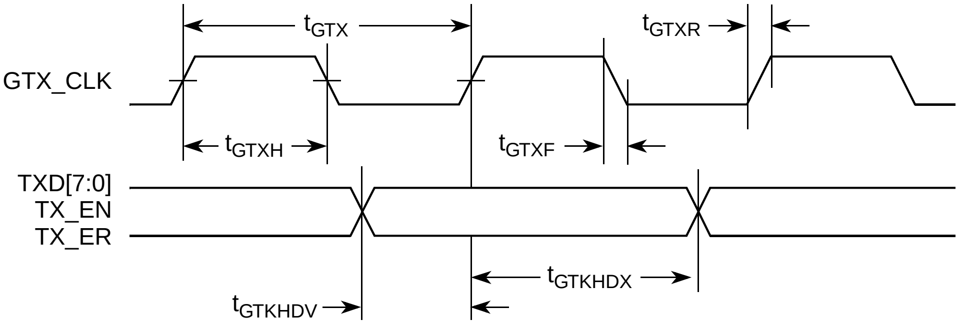


Figure 8. GMII Transmit AC Timing Diagram

8.2.2.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

Table 27. GMII Receive AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	35	—	75	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0	—	—	ns
RX_CLK clock rise (20%-80%)	t_{GRXR}[2]	—	—	1.0	ns
RX_CLK clock fall time (80%-20%)	t_{GRXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 9 provides the AC test load for eTSEC.

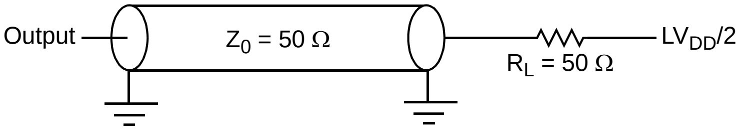


Figure 9. eTSEC AC Test Load

Table 34. RMII Transmit AC Timing Specifications (continued)

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TSEC*n*_TX_CLK to RMII data TXD[1:0], TX_EN delay	t_{RMTDX}	1.0	—	10.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 18 shows the RMII transmit AC timing diagram.

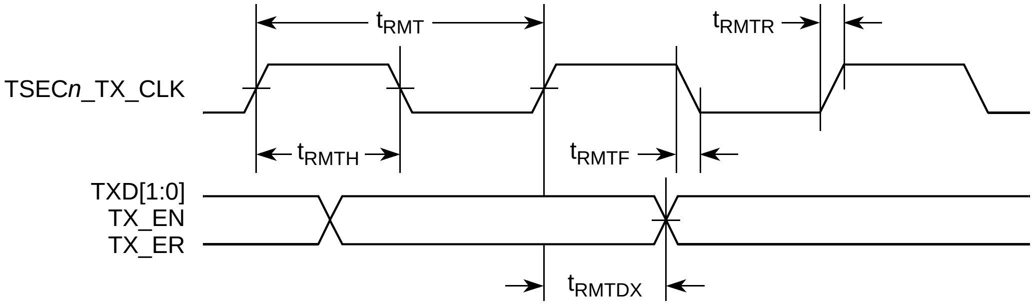


Figure 18. RMII Transmit AC Timing Diagram

8.2.7.2 RMII Receive AC Timing Specifications

Table 35. RMII Receive AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TSEC*n*_TX_CLK clock period	t_{RMR}	15.0	20.0	25.0	ns
TSEC*n*_TX_CLK duty cycle	t_{RMRH}	35	50	65	%
TSEC*n*_TX_CLK peak-to-peak jitter	t_{RMRJ}	—	—	250	ps
Rise time TSEC*n*_TX_CLK(20%–80%)	t_{RMRR}	1.0	—	2.0	ns
Fall time TSEC*n*_TX_CLK (80%–20%)	t_{RMRF}	1.0	—	2.0	ns
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK rising edge	t_{RMRDV}	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK rising edge	t_{RMRDX}	2.0	—	—	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 19 provides the AC test load for eTSEC.

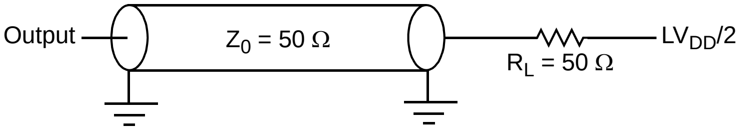


Figure 19. eTSEC AC Test Load

Figure 20 shows the RMII receive AC timing diagram.

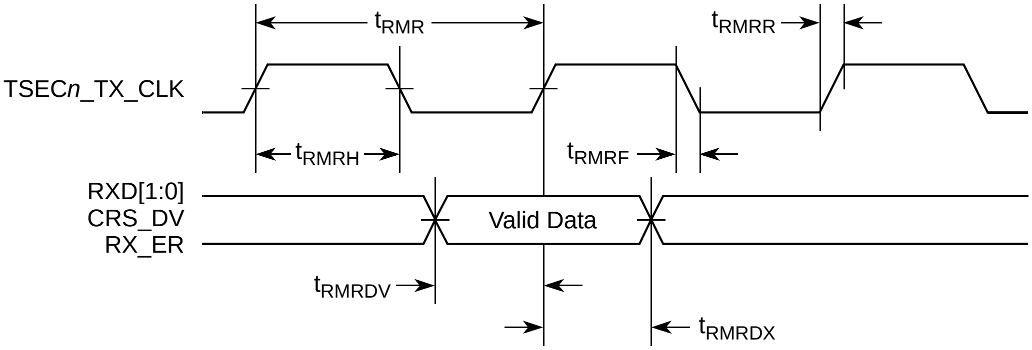


Figure 20. RMII Receive AC Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}^1 = 0 V or V_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (V_{IN}^1 = 0 V or V_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 41 describes the timing parameters of the local bus interface at BV_{DD} = 2.5 V.

Table 41. Local Bus Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/UPWAIT)	$t_{LBIVKH1}$	1.9	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.1	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.3	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.4	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.8	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.6	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Figure 22 provides the AC test load for the local bus.

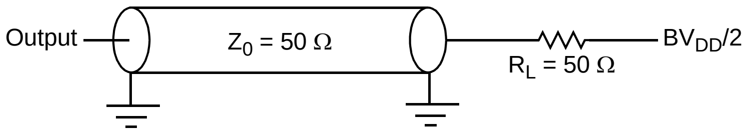


Figure 22. Local Bus AC Test Load

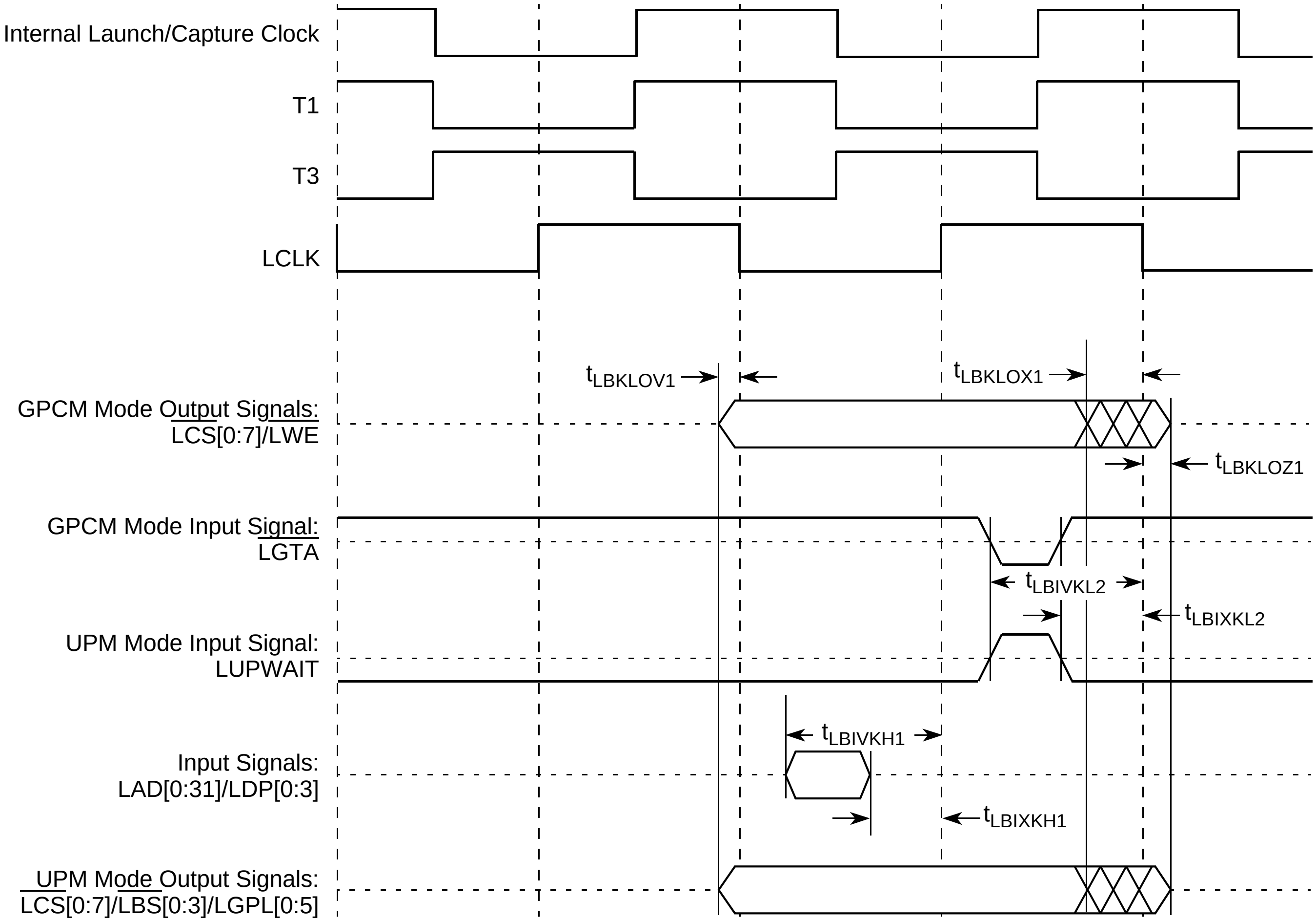


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

Table 43. JTAG DC Electrical Characteristics

Parameter	Symbol[1]	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN}.

12.2 JTAG AC Electrical Specifications

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 32.

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)[1]

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	6
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times:				ns	4
Boundary-scan data	t_{JTDVKH}	4	—		
TMS, TDI	t_{JTIVKH}	0	—		
Input hold times:				ns	4
Boundary-scan data	t_{JTDXKH}	20	—		
TMS, TDI	t_{JTIXKH}	25	—		

Figure 43 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with SerDes reference clock input's DC requirement.

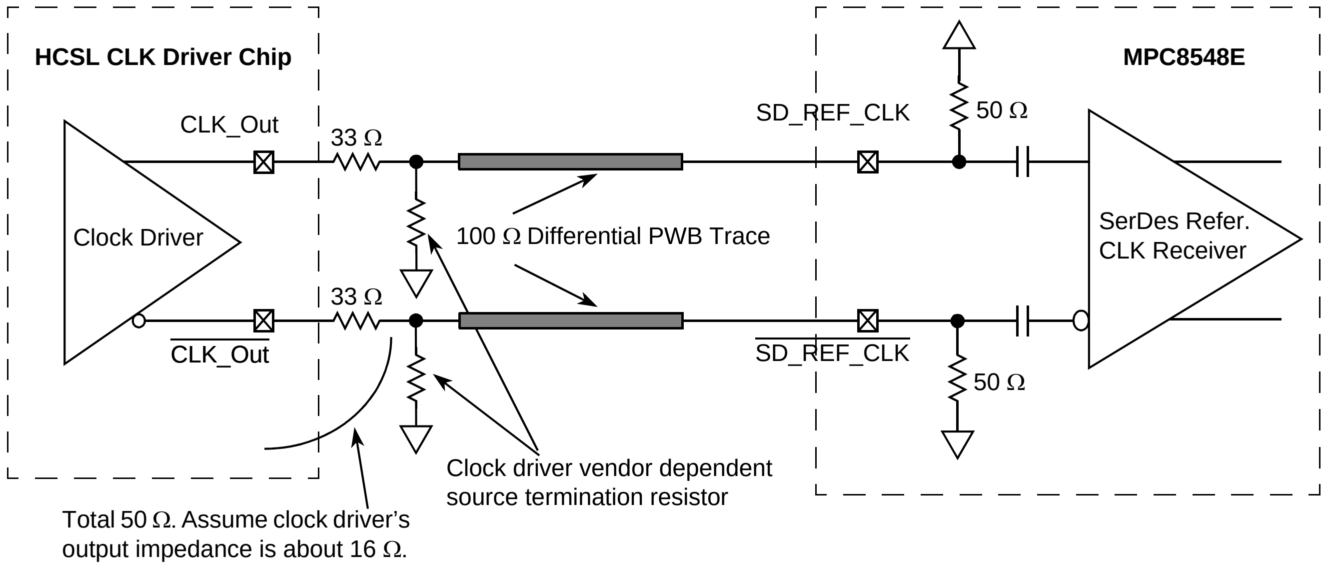


Figure 43. DC-Coupled Differential Connection with HCSL Clock Driver (Reference Only)

Figure 44 shows the SerDes reference clock connection reference circuits for LVDS type clock driver. Since LVDS clock driver's common mode voltage is higher than the SerDes reference clock input's allowed range (100–400 mV), AC-coupled connection scheme must be used. It assumes the LVDS output driver features 50-Ω termination resistor. It also assumes that the LVDS transmitter establishes its own common mode level without relying on the receiver or other external component.

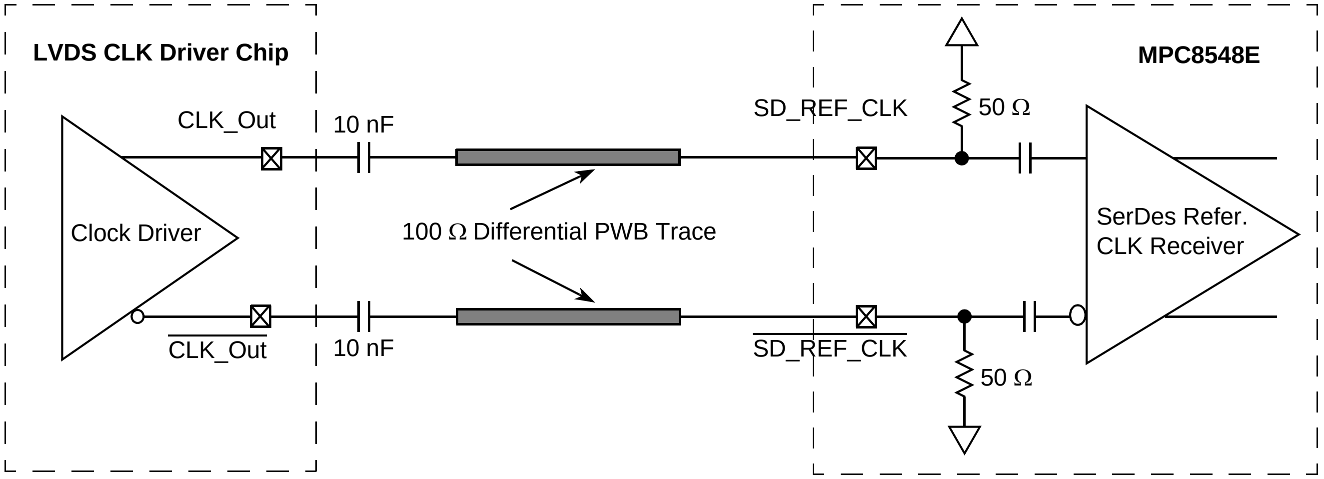


Figure 44. AC-Coupled Differential Connection with LVDS Clock Driver (Reference Only)

Figure 45 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with the SerDes reference clock input's DC requirement, AC-coupling must be used. Figure 45 assumes that the LVPECL clock driver's output impedance is 50 Ω. R1 is used to DC-bias the LVPECL outputs prior

16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected must provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver must be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

The detailed AC requirements of the SerDes reference clocks are defined by each interface protocol based on application usage. See the following sections for detailed information:

- Section 17.2, “AC Requirements for PCI Express SerDes Clocks”
- Section 18.2, “AC Requirements for Serial RapidIO SD_REF_CLK and SD_REF_CLK”

16.2.4.1 Spread Spectrum Clock

SD_REF_CLK/$\overline{\text{SD\_REF\_CLK}}$ are designed to work with a spread spectrum clock (+0% to –0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation must be used.

16.3 SerDes Transmitter and Receiver Reference Circuits

Figure 47 shows the reference circuits for SerDes data lane’s transmitter and receiver.

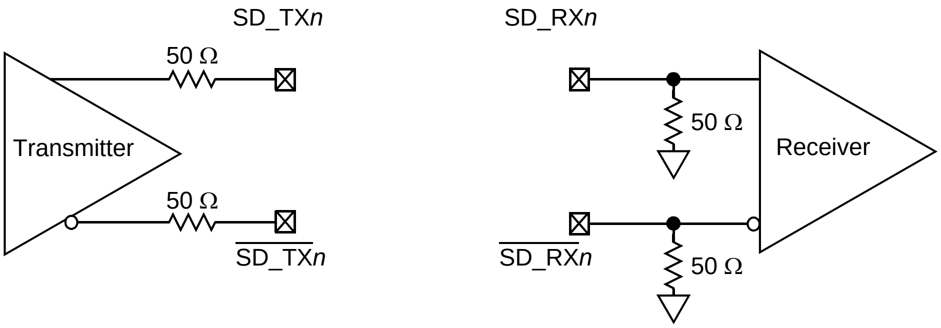


Figure 47. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express, Serial Rapid IO, or SGMII) in this document based on the application usage:

- Section 17, “PCI Express”
- Section 18, “Serial RapidIO”

Note that external an AC coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in the specification of each protocol section.

Table 56. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{TX\text{-}DIFFp\text{-}p}$	Differential peak-to-peak output voltage	0.8	—	1.2	V	$V_{TX\text{-}DIFFp\text{-}p} = 2 \times \lvert V_{TX\text{-}D+} – V_{TX\text{-}D–}\rvert$. See Note 2.
$V_{TX\text{-}DE\text{-}RATIO}$	De- emphasized differential output voltage (ratio)	–3.0	–3.5	–4.0	dB	Ratio of the $V_{TX\text{-}DIFFp\text{-}p}$ of the second and following bits after a transition divided by the $V_{TX\text{-}DIFFp\text{-}p}$ of the first bit after a transition. See Note 2.
$T_{TX\text{-}EYE}$	Minimum TX eye width	0.70	—	—	UI	The maximum transmitter jitter can be derived as $T_{TX\text{-}MAX\text{-}JITTER} = 1 – T_{TX\text{-}EYE} = 0.3$ UI. See Notes 2 and 3.
$T_{TX\text{-}EYE\text{-}MEDIAN\text{-}to\text{-}MAX\text{-}JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.15	UI	Jitter is defined as the measurement variation of the crossing points ($V_{TX\text{-}DIFFp\text{-}p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2 and 3.
$T_{TX\text{-}RISE}$, $T_{TX\text{-}FALL}$	D+/D– TX output rise/fall time	0.125	—	—	UI	See Notes 2 and 5.
$V_{TX\text{-}CM\text{-}ACp}$	RMS AC peak common mode output voltage	—	—	20	mV	$V_{TX\text{-}CM\text{-}ACp} = \mathrm{RMS}(\lvert V_{TXD+} + V_{TXD–}\rvert/2 – V_{TX\text{-}CM\text{-}DC})$ $V_{TX\text{-}CM\text{-}DC} = \mathrm{DC}_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D–}\rvert/2$. See Note 2.
$V_{TX\text{-}CM\text{-}DC\text{-}ACTIVE\text{-}IDLE\text{-}DELTA}$	Absolute delta of dc common mode voltage during L0 and electrical idle	0	—	100	mV	$\lvert V_{TX\text{-}CM\text{-}DC\ (during\ L0)} + V_{TX\text{-}CM\text{-}Idle\text{-}DC\ (during\ electrical\ idle)}\rvert \leq 100$ mV $V_{TX\text{-}CM\text{-}DC} = \mathrm{DC}_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D–}\rvert/2$ [L0] $V_{TX\text{-}CM\text{-}Idle\text{-}DC} = \mathrm{DC}_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D–}\rvert/2$ [electrical idle] See Note 2.
$V_{TX\text{-}CM\text{-}DC\text{-}LINE\text{-}DELTA}$	Absolute delta of DC common mode between D+ and D–	0	—	25	mV	$\lvert V_{TX\text{-}CM\text{-}DC\text{-}D+} – V_{TX\text{-}CM\text{-}DC\text{-}D–}\rvert \leq 25$ mV $V_{TX\text{-}CM\text{-}DC\text{-}D+} = \mathrm{DC}_{(avg)}$ of $\lvert V_{TX\text{-}D+}\rvert$ $V_{TX\text{-}CM\text{-}DC\text{-}D–} = \mathrm{DC}_{(avg)}$ of $\lvert V_{TX\text{-}D–}\rvert$. See Note 2.
$V_{TX\text{-}IDLE\text{-}DIFFp}$	Electrical idle differential peak output voltage	0	—	20	mV	$V_{TX\text{-}IDLE\text{-}DIFFp} = \lvert V_{TX\text{-}IDLE\text{-}D+} – V_{TX\text{-}IDLE\text{-}D–}\rvert \leq 20$ mV. See Note 2.
$V_{TX\text{-}RCV\text{-}DETECT}$	The amount of voltage change allowed during receiver detection	—	—	600	mV	The total amount of voltage change that a transmitter can apply to sense whether a low impedance receiver is present. See Note 6.

802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE Std. 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

18.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (baud frequency)/1667 is applied to the jitter. The data pattern for template measurements is the continuous jitter test pattern (CJPAT) defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. The amount of data represented in the eye shall be adequate to ensure that the bit error ratio is less than 10^{-12}. The eye pattern shall be measured with AC coupling and the compliance template centered at 0 V differential. The left and right edges of the template shall be aligned with the mean zero crossing points of the measured data eye. The load for this test shall be 100-Ω resistive ± 5% differential to 2.5 GHz.

18.9.2 Jitter Test Measurements

For the purpose of jitter measurement, the effects of a single-pole high pass filter with a 3 dB point at (baud frequency)/1667 is applied to the jitter. The data pattern for jitter measurements is the Continuous Jitter test pattern (CJPAT) pattern defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. Jitter shall be measured with AC coupling and at 0 V differential. Jitter measurement for the transmitter (or for calibration of a jitter tolerance setup) shall be performed with a test procedure resulting in a BER curve such as that described in Annex 48B of IEEE 802.3ae.

18.9.3 Transmit Jitter

Transmit jitter is measured at the driver output when terminated into a load of 100 Ω resistive ± 5% differential to 2.5 GHz.

18.9.4 Jitter Tolerance

Jitter tolerance is measured at the receiver using a jitter tolerance test signal. This signal is obtained by first producing the sum of deterministic and random jitter defined in Section 18.7, “Receiver Specifications,” and then adjusting the signal amplitude until the data eye contacts the 6 points of the minimum eye opening of the receive template shown in Figure 54 and Table 69. Note that for this to occur, the test signal must have vertical waveform symmetry about the average value and have horizontal symmetry (including jitter) about the mean zero crossing. Eye template measurement requirements are as defined above. Random jitter is calibrated using a high pass filter with a low frequency corner at 20 MHz and a 20 dB/decade roll-off below this. The required sinusoidal jitter specified in Section 18.7, “Receiver Specifications,” is then added to the signal and the test load is replaced by the receiver being tested.

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ64}}$/$\overline{\text{PCI2\_FRAME}}$	AF14	I/O	OV_{DD}	2, 5, 10
$\overline{\text{PCI1\_ACK64}}$/$\overline{\text{PCI2\_DEVSEL}}$	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
$\overline{\text{PCI2\_IRDY}}$	AD26	I/O	OV_{DD}	2
$\overline{\text{PCI2\_PERR}}$	AD25	I/O	OV_{DD}	2
$\overline{\text{PCI2\_GNT}}$[4:1]	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI2\_GNT0}}$	AG25	I/O	OV_{DD}	—
$\overline{\text{PCI2\_SERR}}$	AD24	I/O	OV_{DD}	2,4
$\overline{\text{PCI2\_STOP}}$	AF24	I/O	OV_{DD}	2
$\overline{\text{PCI2\_TRDY}}$	AD27	I/O	OV_{DD}	2
$\overline{\text{PCI2\_REQ}}$[4:1]	AD28, AE27, W17, AF26	I	OV_{DD}	—
$\overline{\text{PCI2\_REQ0}}$	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—
$\overline{\text{MWE}}$	E7	O	GV_{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
TEST_SEL	AH14	I	OV_{DD}	109
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—